



NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3050 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

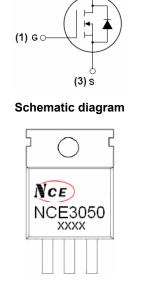
General Features

- V_{DS} =30V,I_D =50A
 R_{DS(ON)} < 9mΩ @ V_{GS}=10V
 R_{DS(ON)} < 15mΩ @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!



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Marking and pin Assignment



Package Marking And Ordering Information

	<i></i>				
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3050	NCE3050	TO-220-3L	-	-	-

Absolute Maximum Ratings (TA=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	50	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	35	А
Pulsed Drain Current	I _{DM}	140	А
Maximum Power Dissipation	PD	60	W
Derating factor		0.4	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	70	mJ



Pb Free Product

NCE3050

Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2) R _{0JC} 2.5 °C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·	·				
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.6	3	V
Drain Course On Chata Desistence	В	V _{GS} =10V, I _D =25A	-	8	11	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =5V, I _D =20A	-	10	16	11112
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)	·	·				
Input Capacitance	C _{lss}		-	2000	-	PF
Output Capacitance	Coss	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	280	-	PF
Reverse Transfer Capacitance	C _{rss}		-	160	-	PF
Switching Characteristics (Note 4)		·	-			
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V _{DD} =15V,I _D =20A	-	8	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =1.8 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	\/ _40\/↓ _05A	-	23	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =10V,I _D =25A,	-	7	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	4.5	-	nC
Drain-Source Diode Characteristics	·	·				
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =25A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	40	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	22	35	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs(Note3)	-	12	20	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negli	gible (turi	n-on is do	ominated b	y LS+LD)

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

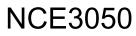
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}$,V_DD=15V,V_G=10V,L=1mH,Rg=25 Ω

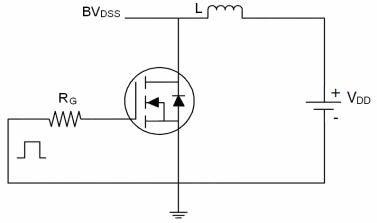


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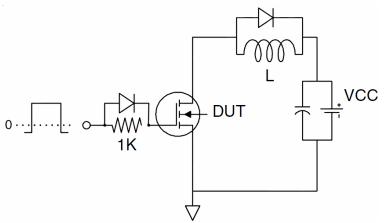


Test circuit

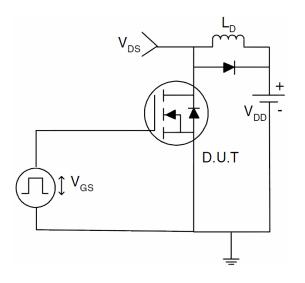
1) E_{AS} test Circuits



2) Gate charge test Circuit:



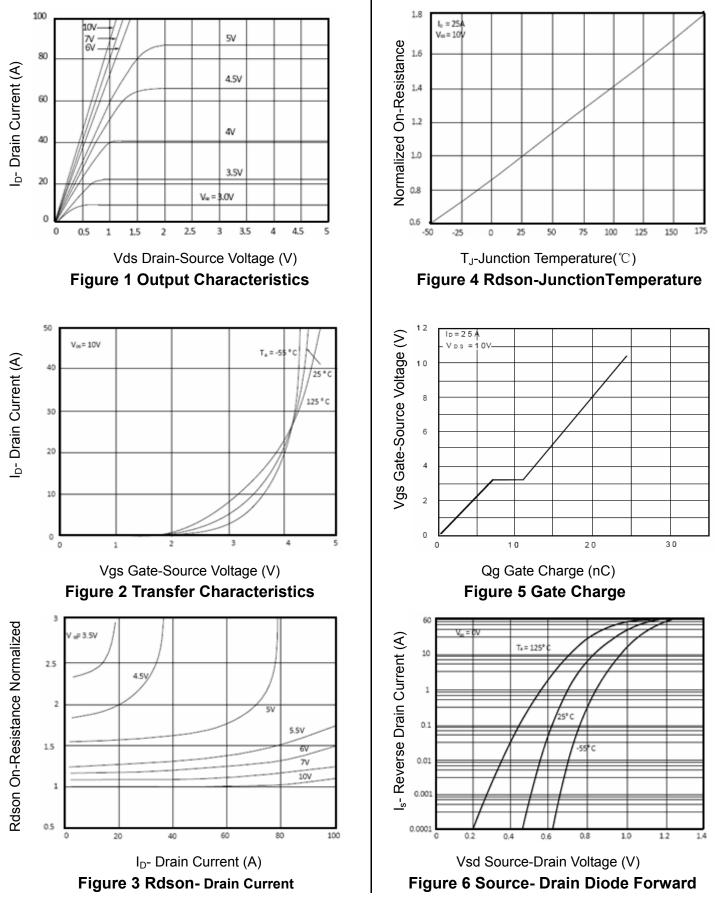
3) Switch Time Test Circuit:



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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)





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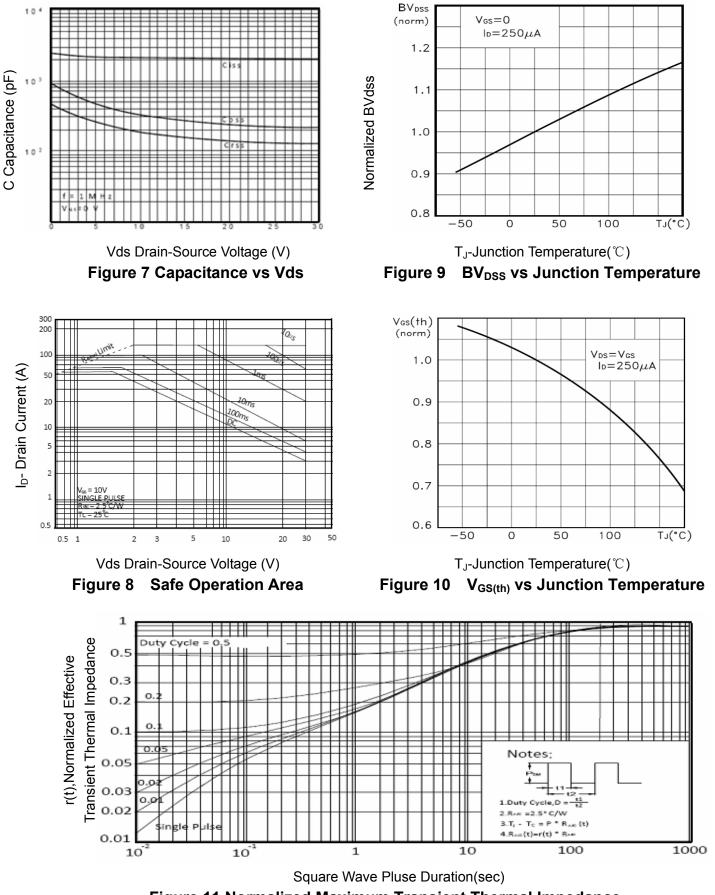


Figure 11 Normalized Maximum Transient Thermal Impedance

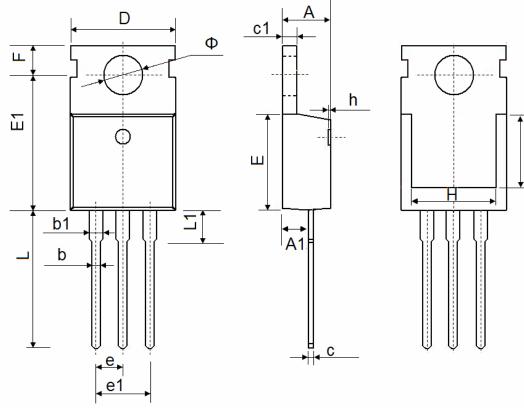
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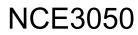
TO-220-3L Package Information



Cumhal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	0 TYP.	0.100) TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	







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